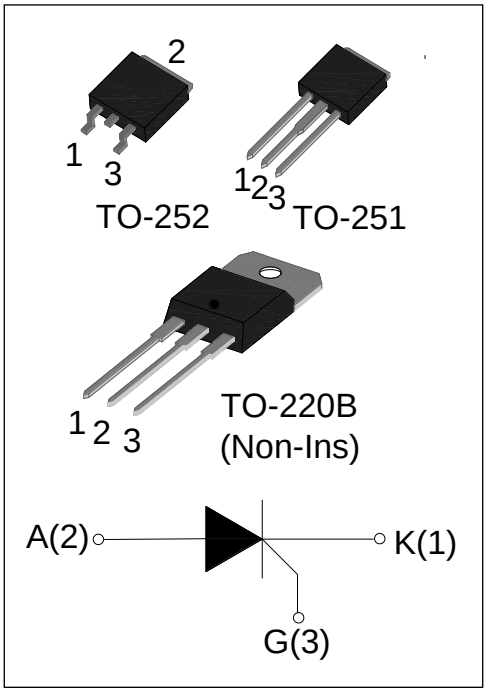
JX080 Series Sensitive gate SCRs

Rev.3.0

DESCRIPTION:

The JX080 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.



MAIN FEATURES

Symbol	Value	Unit
V_{DRM}/ V_{RRM}	600/800	V
$I_{T(RMS)}$	8	A
I_{GT}	≤200	μA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 110	℃
Repetitive peak off-state voltage		V_{DRM}	600/800	V
Repetitive peak reverse voltage		V_{RRM}	600/800	V
RMS on-state current	TO-251/ TO-252/ TO-220B(Non-Ins) (T_C=100℃)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (tp=10ms)		I_{TSM}	70	A
I^2t value for fusing (tp=10ms)		I^2t	24.5	A^2s
Critical rate of rise of on-state current		dI/dt	50	A/μs
Peak gate current (tp=20μs, Tj=110℃)		I_{GM}	4	A
Peak gate power (tp=20μs, Tj=110℃)		P_{GM}	5	W
Average gate power dissipation(T_j=110℃)		$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	50	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	V_D=V_{DRM} T_j=110℃	0.2	-	-	V
I_L	I_G=1.2 I_{GT}	-	-	6	mA
I_H	I_T=0.05A	-	-	5	mA
dV/dt	V_D=2/3V_{DRM} T_j=110℃ R_{GK}=1KΩ	10	-	-	V/μs

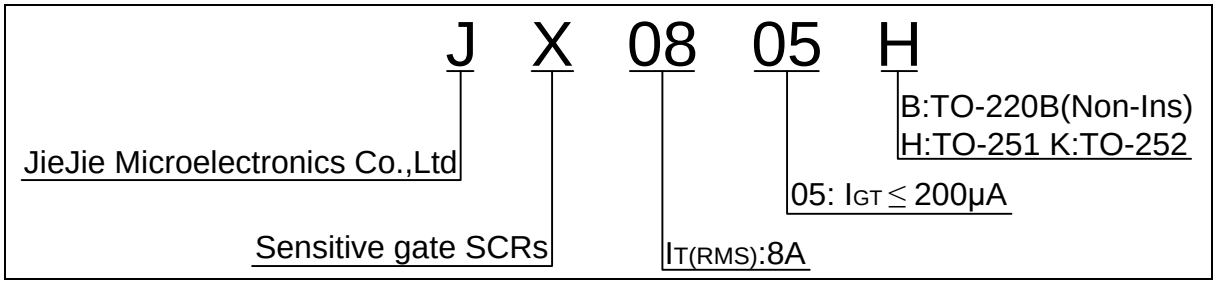
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_T=16A tp=380μs	T_j=25℃	1.5	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=110℃	100	μA

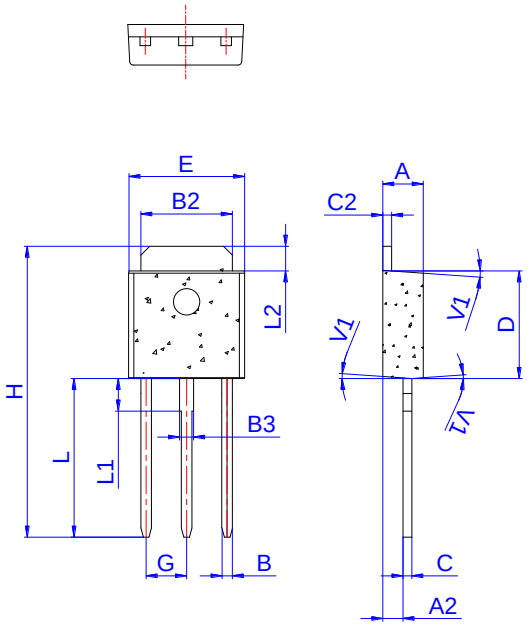
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-251/ TO-252	20	℃/W
		TO-220B(Non-Ins)	15	

ORDERING INFORMATION

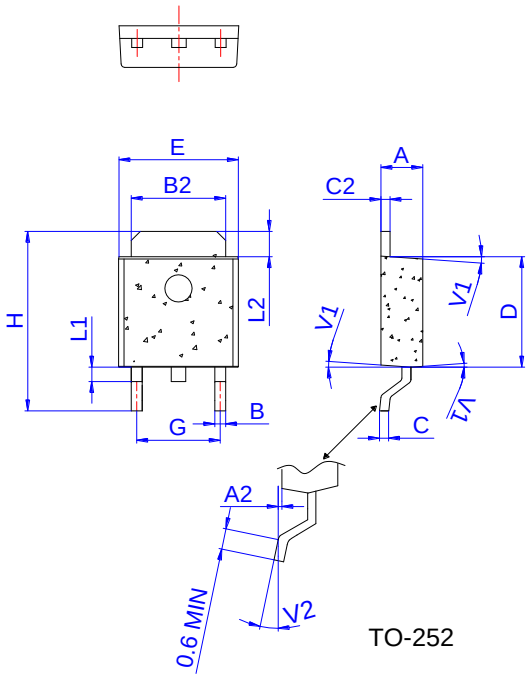


PACKAGE MECHANICAL DATA



TO-251

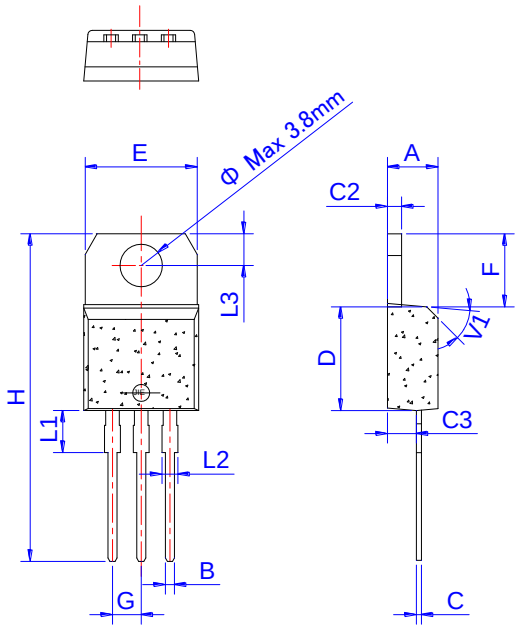
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

FIG.1 Maximum power dissipation versus RMS on-state current

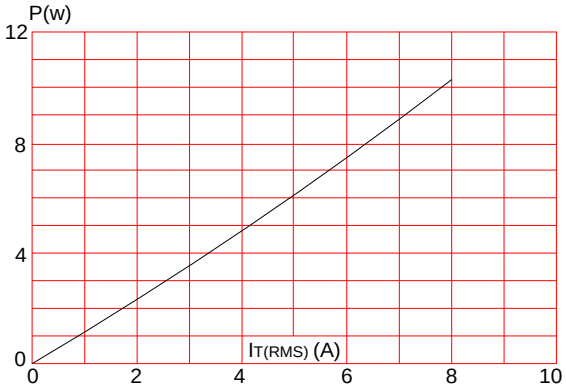


FIG.2: RMS on-state current versus case temperature

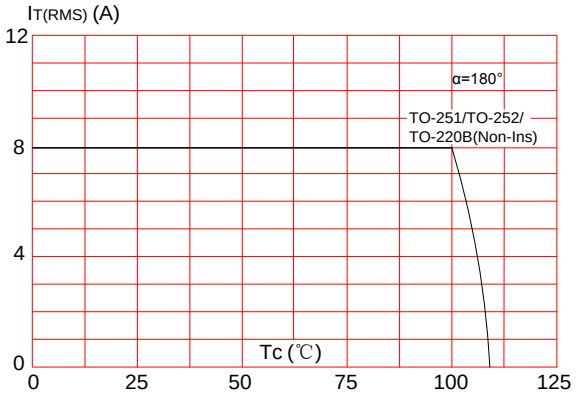


FIG.3: Surge peak on-state current versus number of cycles

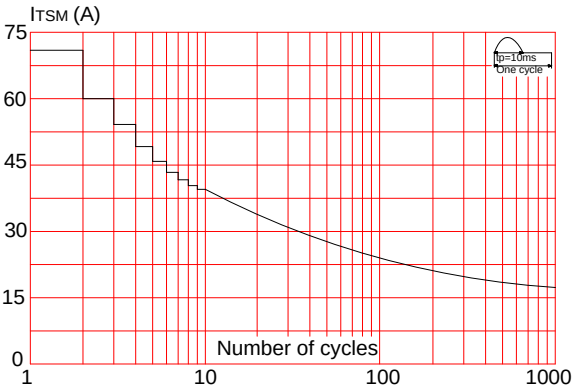


FIG.4: On-state characteristics (maximum values)

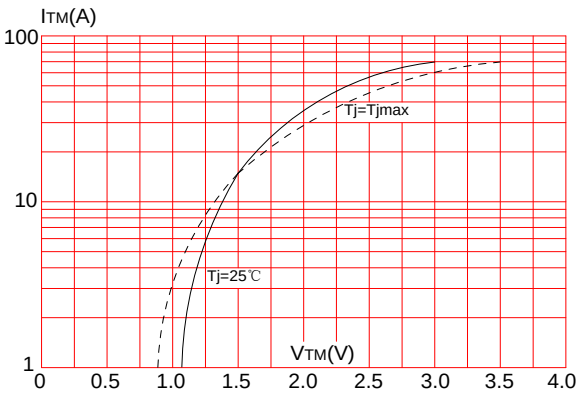


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms, and corresponging value of I^2t (dI/dt < 50A/μs)

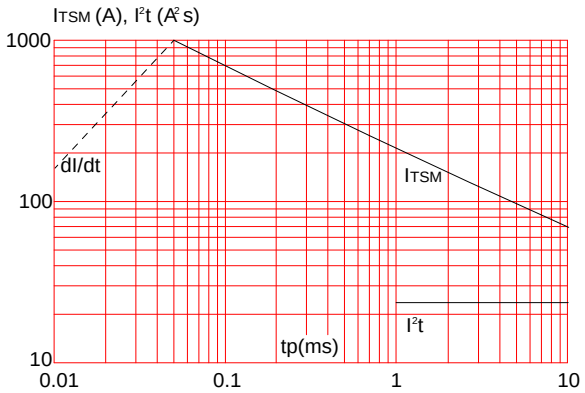
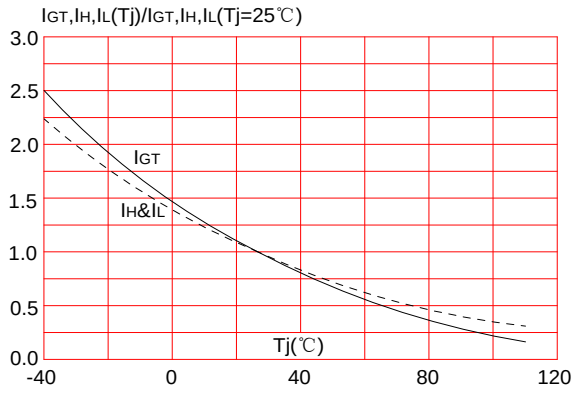


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement. Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information.

This document is the third version which is made in 6-June-2015. This document supersedes and replaces all information previously supplied.

is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.

Copyright ©2015 Jiangsu JieJie Microelectronics Co.,Ltd. Printed All rights reserved.